

Yi Hojoon

List of Publications by Year in descending order

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papers

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1478505

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295
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhanced Electron Heat Conduction in TaS ₃ 1D Metal Wire. <i>Materials</i> , 2021, 14, 4477.	2.9	2
2	Thickness effect on low-power driving of MoS ₂ transistors in balanced double-gate fields. <i>Nanotechnology</i> , 2020, 31, 255201.	2.6	2
3	Wiedemann-Franz law of Cu-coated carbon fiber. <i>Carbon</i> , 2020, 162, 339-345.	10.3	11
4	Impact of Heat Treatment on a Hetero-Stacked MoS ₂ /h-BN Field-Effect Transistor. <i>IEEE Electron Device Letters</i> , 2019, 40, 1626-1629.	3.9	1
5	Gas adsorbates are Coulomb scatterers, rather than neutral ones, in a monolayer MoS ₂ field effect transistor. <i>Nanoscale</i> , 2018, 10, 10856-10862.	5.6	7
6	Thickness-dependent carrier mobility of ambipolar MoTe ₂ : Interplay between interface trap and Coulomb scattering. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	42
7	Graphene-CdSe quantum dot hybrid as a platform for the control of carrier temperature. <i>FlatChem</i> , 2017, 6, 77-82.	5.6	9
8	Tunable Mobility in Double-Gated MoTe ₂ Field-Effect Transistor: Effect of Coulomb Screening and Trap Sites. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 29185-29192.	8.0	31
9	Suppression of Interfacial Current Fluctuation in MoTe ₂ Transistors with Different Dielectrics. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 19092-19099.	8.0	35